Supplemental Document

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Multiscale modeling of Gallium Nitride Atomic Layer Etching in chlorinated plasmas: a combined dynamic global model, Ab-initio and kinetic Monte Carlo approaches

T. Rasoanarivo[1,2], C. Mannequin[1], I. Braems[1], F. Roqueta[2], M. Boufnichel[2], A. Rhallabi[1]

[1]Nantes Université, CNRS, - Institut des Matériaux de Nantes Jean Rouxel, IMN, F-44000 Nantes, France

[2]STMicroelectronics Tours, 10 rue Thalès de Milet, 37100

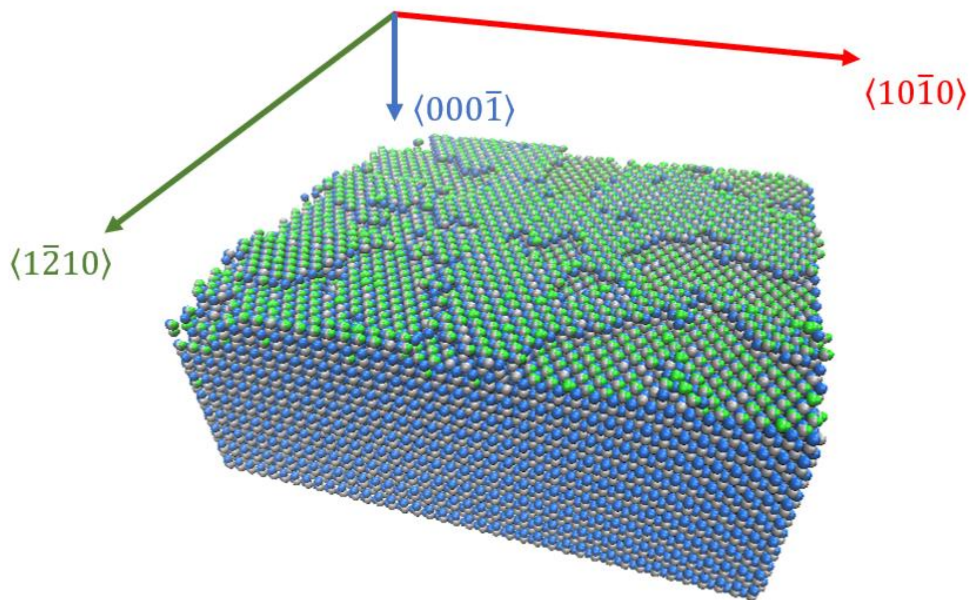

Fig 1. Snapshot of GaN surface (127 Å x 127 Å x 52 Å) during ALE in chlorinated plasmas by kMC simulations. **Modification step at the 16th cyle**. Green : Cl atoms, Blue : Ga atoms, Grey : N atoms.

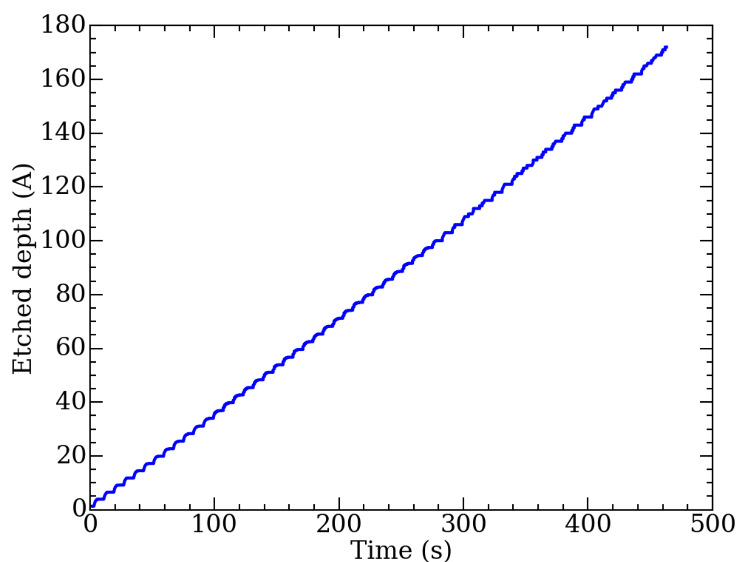

Fig 2. GaN Etched depth calculated by our multiscale model. **Each individual step on the figure corresponds to one ALE cycle.**